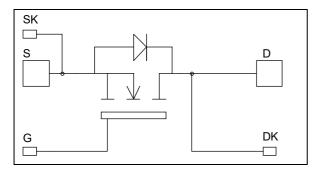
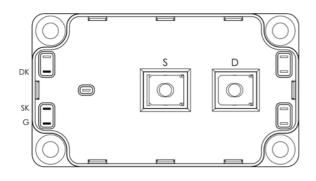


## Single Switch MOSFET Power Module





## $V_{DSS} = 500V$ $R_{DSon} = 9 \text{ m}\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}\text{C}$ $I_D = 497\text{A} @ \text{Tc} = 25^{\circ}\text{C}$

### Application

- Welding converters
  - Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Power MOS 7<sup>®</sup> FREDFETs
  - Low R<sub>DSon</sub>
    - Low input and Miller capacitance
    - Low gate charge
    - Fast intrinsic reverse diode
    - Avalanche energy rated
    - Very rugged
  - Kelvin source for easy drive
  - Very low stray inductance
  - M5 power connectors
  - High level of integration
  - AlN substrate for improved thermal performance

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>DSS</sub>	Drain - Source Voltage		500	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	497	
I <sub>D</sub>	Continuous Drain Current	$T_c = 80^{\circ}C$	371	А
I <sub>DM</sub>	Pulsed Drain current		1988	
V <sub>GS</sub>	Gate - Source Voltage		$\pm 30$	V
R <sub>DSon</sub>	Drain - Source ON Resistance		10	mΩ
PD	Power Dissipation $T_c = 25^{\circ}C$		5000	W
I <sub>AR</sub>	Avalanche current (repetitive and non repetitive)		71	А
E <sub>AR</sub>	Repetitive Avalanche Energy		50	mI
E <sub>AS</sub>	Single Pulse Avalanche Energy	3000	mJ	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			600	μΑ
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 248.5A$		9	10	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 30 \text{mA}$	3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±450	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Ciss	Input Capacitance	$V_{GS} = 0V$		63.3		
Coss	Output Capacitance	$V_{DS} = 25V$		12.4		nF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.63		
$Q_{g}$	Total gate Charge	$V_{GS} = 10V$		1200		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 250V$		300		
$Q_{gd}$	Gate – Drain Charge	I <sub>D</sub> =497A		630		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive switching @ 125°C		21		
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$		42		
$T_{d(off)}$	Turn-off Delay Time	$\begin{split} V_{Bus} &= 333V\\ I_D &= 497A\\ R_G &= 0.5\Omega \end{split}$		96		ns
$T_{\mathrm{f}}$	Fall Time			100		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 497A, R_G = 0.5\Omega$		6		т
$E_{\mathrm{off}}$	Turn-off Switching Energy			6.2		mJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$ , $V_{Bus} = 333V$ $I_D = 497A$ , $R_G = 0.5\Omega$		9.48		
$E_{\rm off}$	Turn-off Switching Energy			6.96		mJ
$R_{thJC}$	Junction to Case Thermal Resistance	e			0.025	°C/W

### Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$			497	٨
	(Body diode)		$Tc = 80^{\circ}C$			371	A
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -497A$				1.3	V
dv/dt	Peak Diode Recovery <b>1</b>					18	V/ns
+	Payama Pagayamy Tima		$T_j = 25^{\circ}C$			300	
t <sub>rr</sub>	Reverse Recovery Time	$I_{\rm S} = -497 A$ $V_{\rm R} = 333 V$	$T_j = 125^{\circ}C$			600	ns
0	Reverse Recovery Charge	$di_s/dt = 600A/\mu s$	$T_j = 25^{\circ}C$		15.6		μC
Q <sub>rr</sub>	Reverse Recovery Charge	,	$T_j = 125^{\circ}C$		60		μυ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. I<sub>S</sub>  $\leq$  - 497A di/dt  $\leq$  700A/ $\mu$ s V<sub>R</sub>  $\leq$  V<sub>DSS</sub> T<sub>j</sub>  $\leq$  150°C

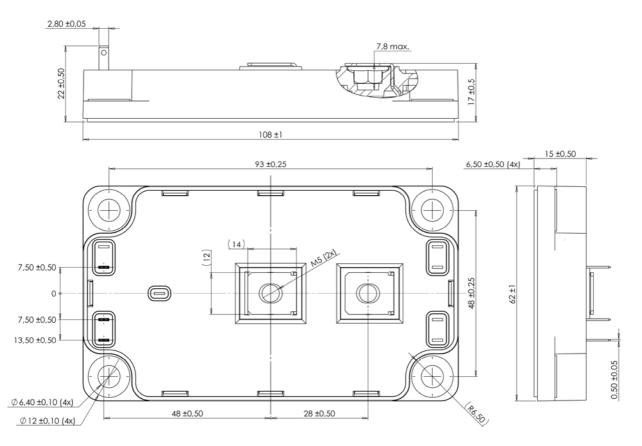


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### Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
TJ	Operating junction temperature range			-40	150	°C
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature			-40	125	
Torque	Mounting torque	To Heatsink	M6	3	5	N.m
Torque		For teminals	M5	2	3.5	18.111
Wt	Package Weight				300	g

### Package outline (dimensions in mm)

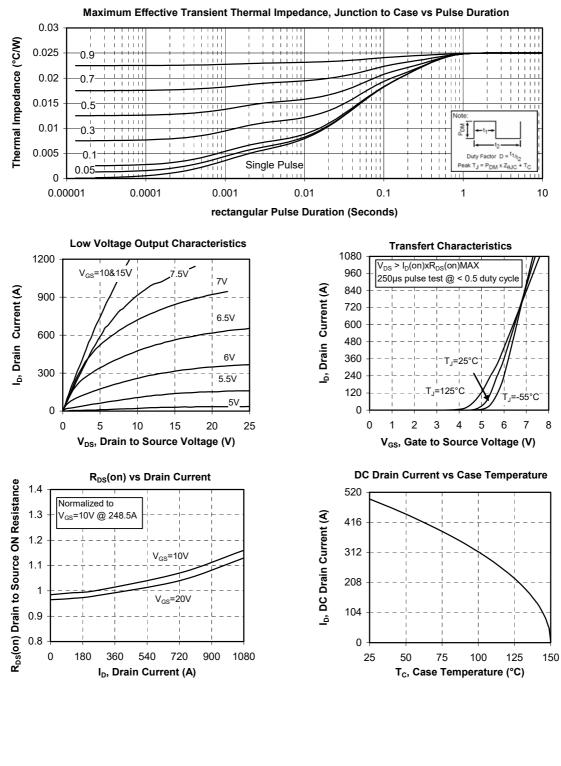


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com



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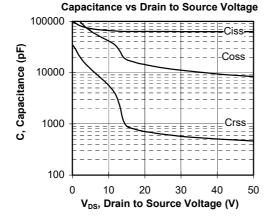
#### **Typical Performance Curve**



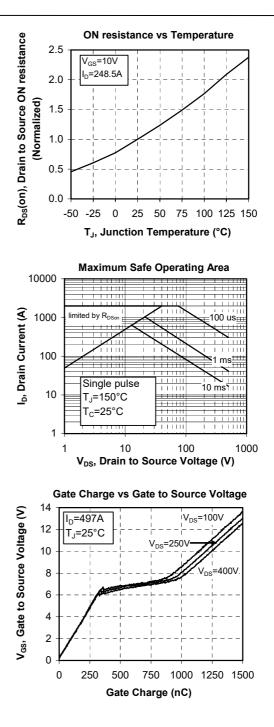


BV<sub>DSS</sub>, Drain to Source Breakdown 1.15 Voltage (Normalized) 1.05 0.95 0.85 -50 -25 0 25 50 75 100 125 150 T<sub>J</sub>, Junction Temperature (°C) **Threshold Voltage vs Temperature** 1.2 V<sub>GS</sub>(TH), Threshold Voltage 1.1 1.0 (Normalized) 0.9 0.8 0.7 0.6 -50 -25 0 25 50 75 100 125 150 T<sub>c</sub>, Case Temperature (°C)

Breakdown Voltage vs Temperature



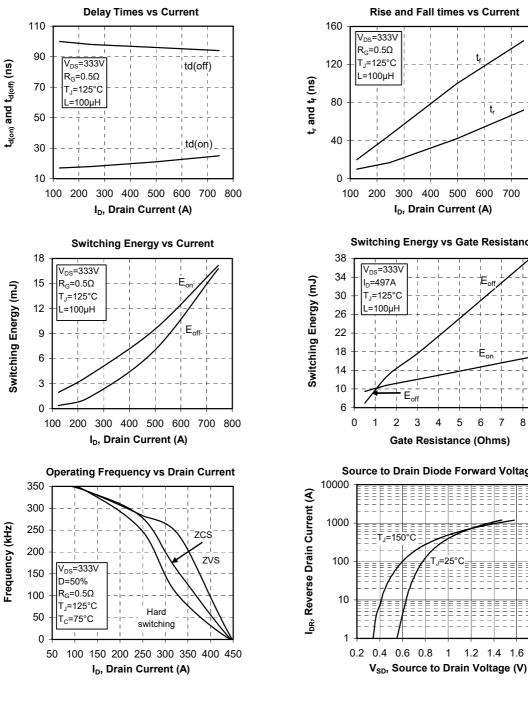
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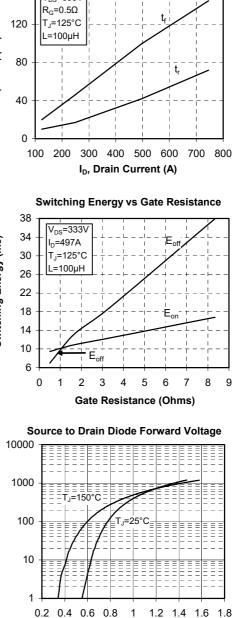




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## **APTM50UM09FAG**







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